

# SHINDENGEN

## VZ Series Power MOSFET

N-Channel Enhancement type

**2SK2491**  
( F20S18VZ )

**180V 20A**

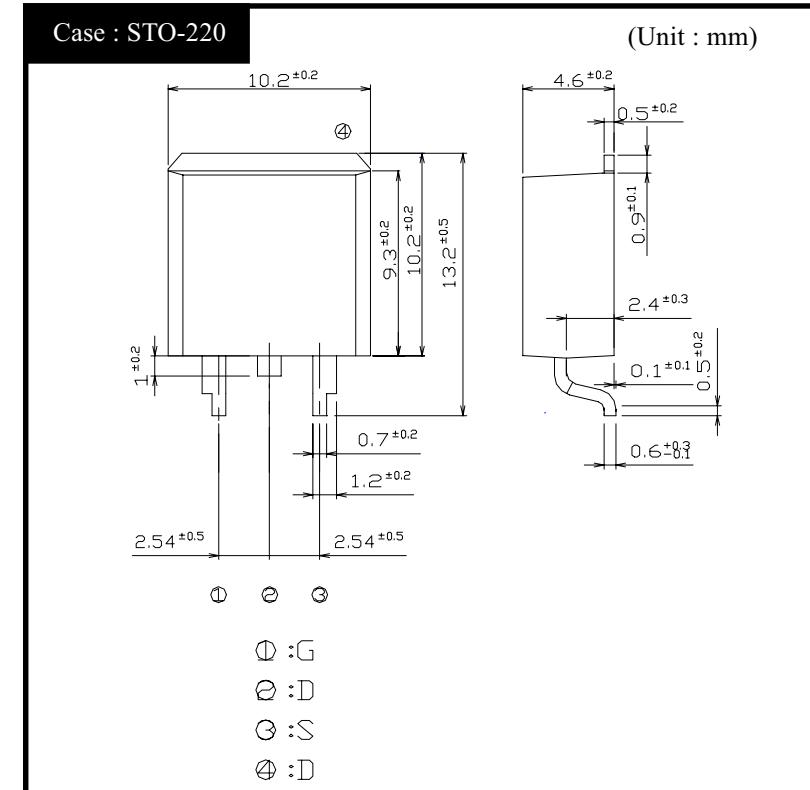
### FEATURES

- Input capacitance ( $C_{iss}$ ) is small.  
Especially, input capacitance at 0 bias is small.
- The static  $R_{ds(on)}$  is small.
- The switching time is fast.

### APPLICATION

- DC/DC converters
- Power supplies of DC 12-24V input
- Product related to  
Integrated Service Digital Network

### OUTLINE DIMENSIONS



### RATINGS

#### ● Absolute Maximum Ratings (T<sub>c</sub> = 25°C)

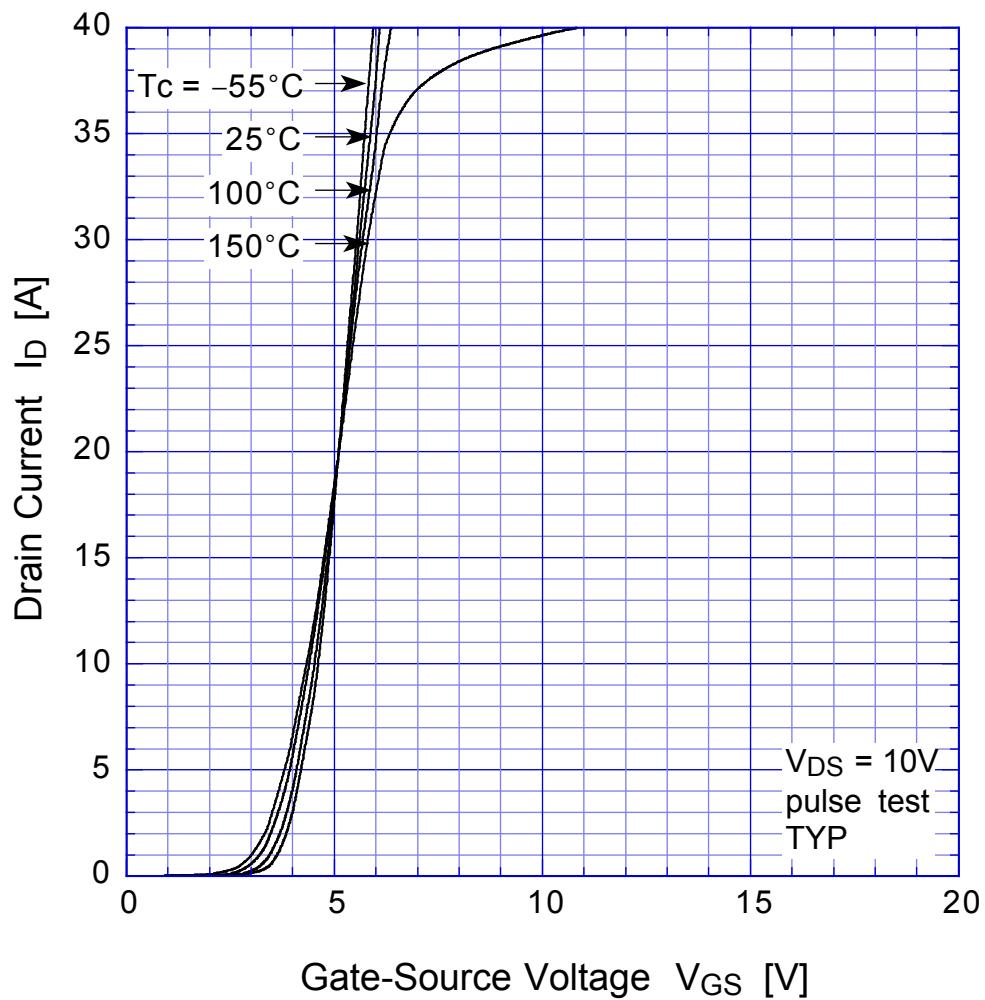
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T <sub>stg</sub>		-55~150	°C
Channel Temperature	T <sub>ch</sub>		150	
Drain-Source Voltage	V <sub>DSS</sub>		180	V
Gate-Source Voltage	V <sub>GSS</sub>		±30	
Continuous Drain Current(DC)	I <sub>D</sub>		20	A
Continuous Drain Current(Peak)	I <sub>DP</sub>		40	
Continuous Source Current(DC)	I <sub>S</sub>		20	
Total Power Dissipation	P <sub>T</sub>		70	W
Single Pulse Avalanche Current	I <sub>AS</sub>	T <sub>ch</sub> = 25°C	20	A

●Electrical Characteristics T<sub>c</sub> = 25°C

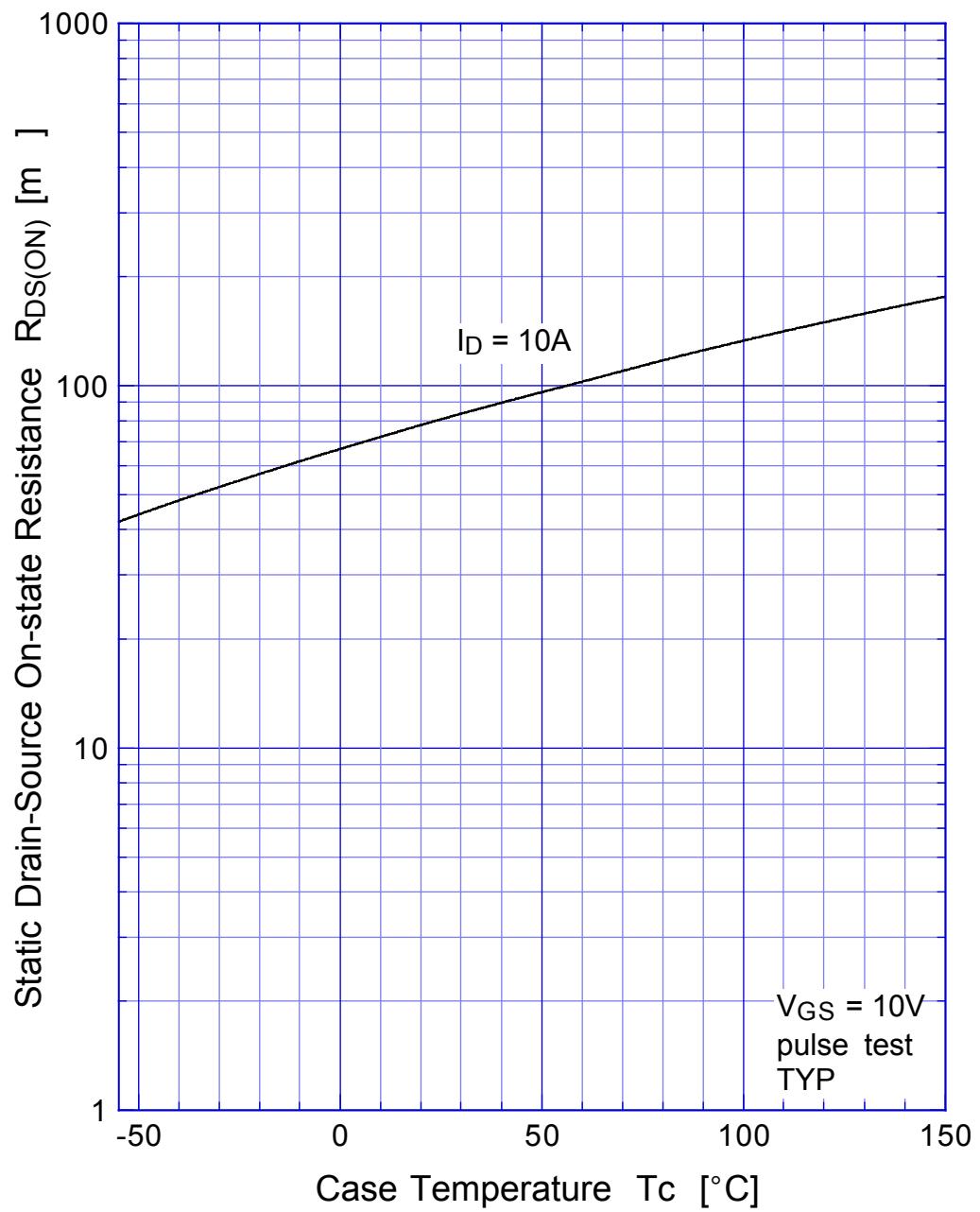
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	ID = 1mA, V <sub>GS</sub> = 0V	180			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 180V, V <sub>GS</sub> = 0V			250	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V			±0.1	
Forward Transconductance	g <sub>s</sub>	ID = 10A, V <sub>DS</sub> = 10V	8.0	15.0		S
Static Drain-Source On-state Resistance	R <sub>DSON</sub>	ID = 10A, V <sub>GS</sub> = 10V		0.08	0.13	Ω
Gate Threshold Voltage	V <sub>TH</sub>	ID = 1mA, V <sub>DS</sub> = 10V	2.0	3.0	4.0	V
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 10A, V <sub>GS</sub> = 0V			1.5	
Thermal Resistance	θ <sub>jc</sub>	junction to case			1.78	°C/W
Total Gate Charge	Q <sub>g</sub>	V <sub>DD</sub> = 150V, V <sub>GS</sub> = 10V, ID = 20A		55		nC
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz		1600		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			190		
Output Capacitance	C <sub>oss</sub>			650		
Turn-On Time	t <sub>on</sub>	ID = 10A, V <sub>GS</sub> = 10V, R <sub>L</sub> = 10Ω		95	190	ns
Turn-Off Time	t <sub>off</sub>			300	600	

# 2SK2491

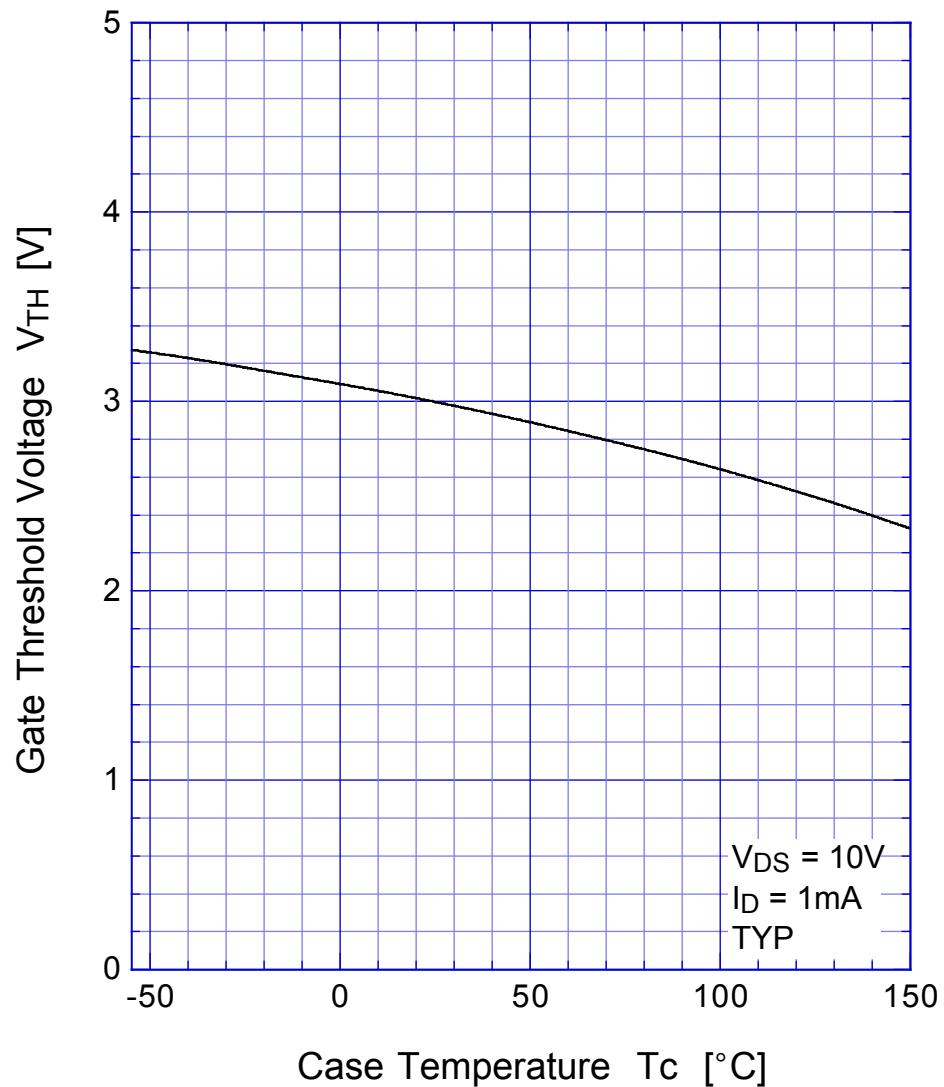
## Transfer Characteristics



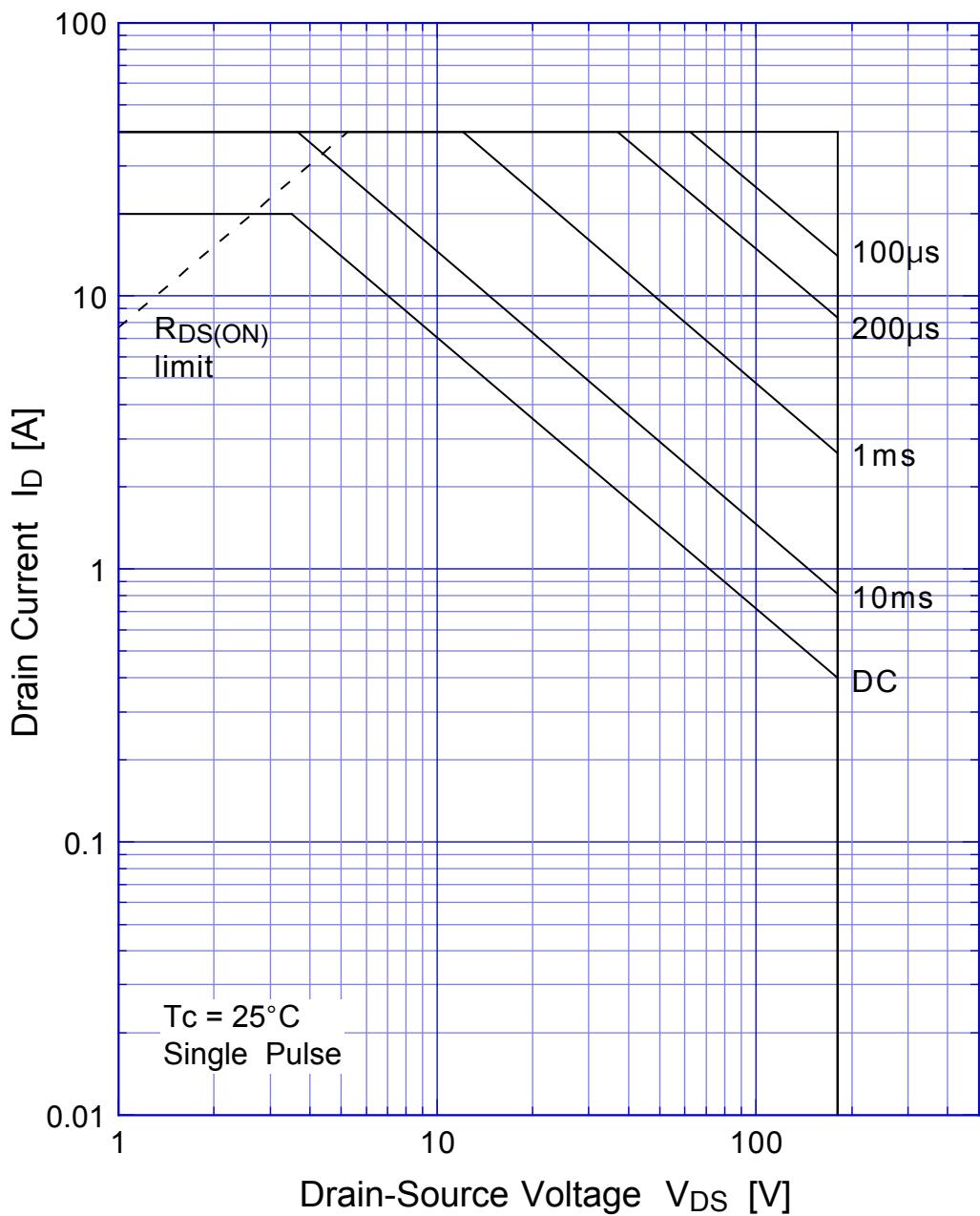
## 2SK2491 Static Drain-Source On-state Resistance



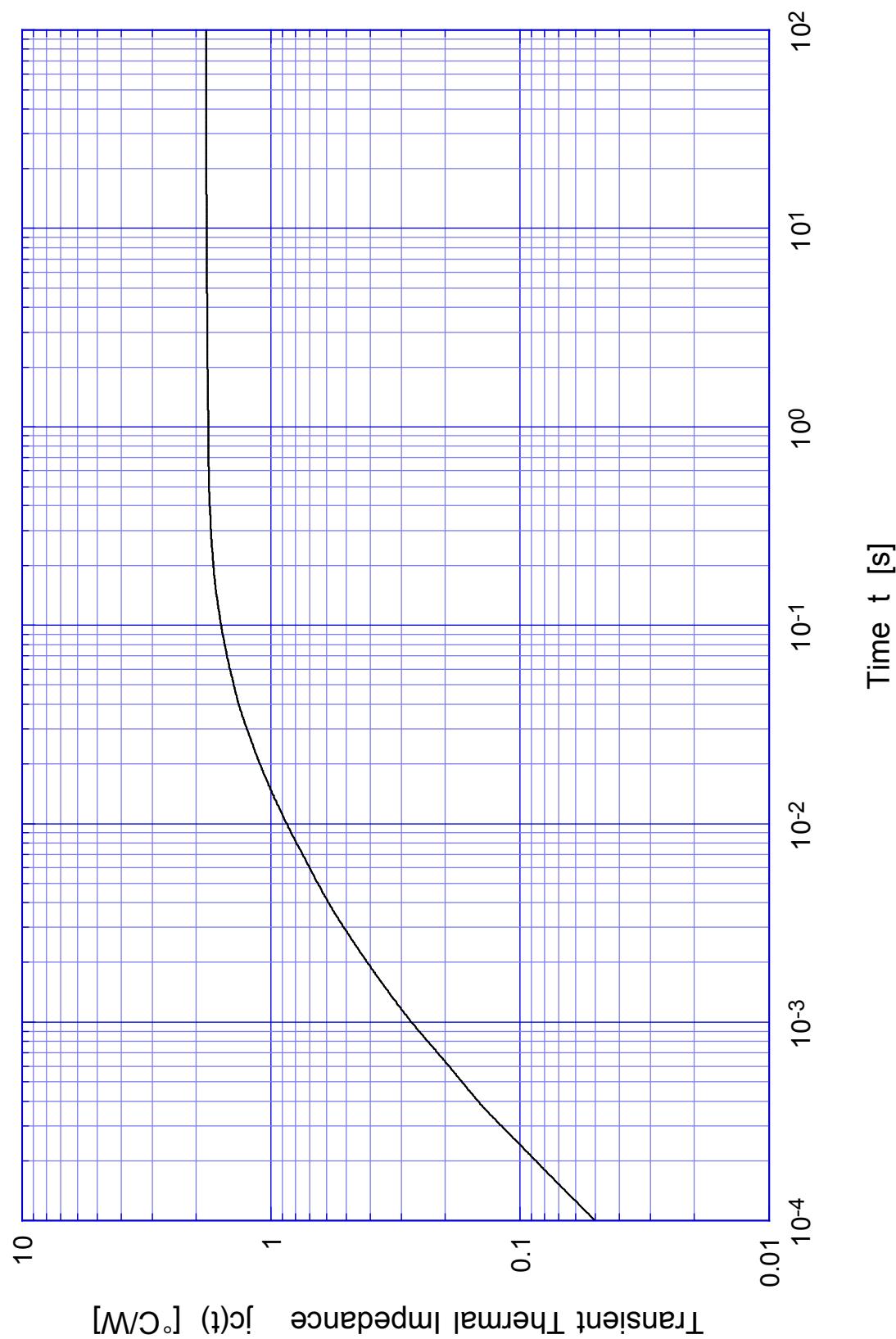
## **2SK2491      Gate Threshold Voltage**



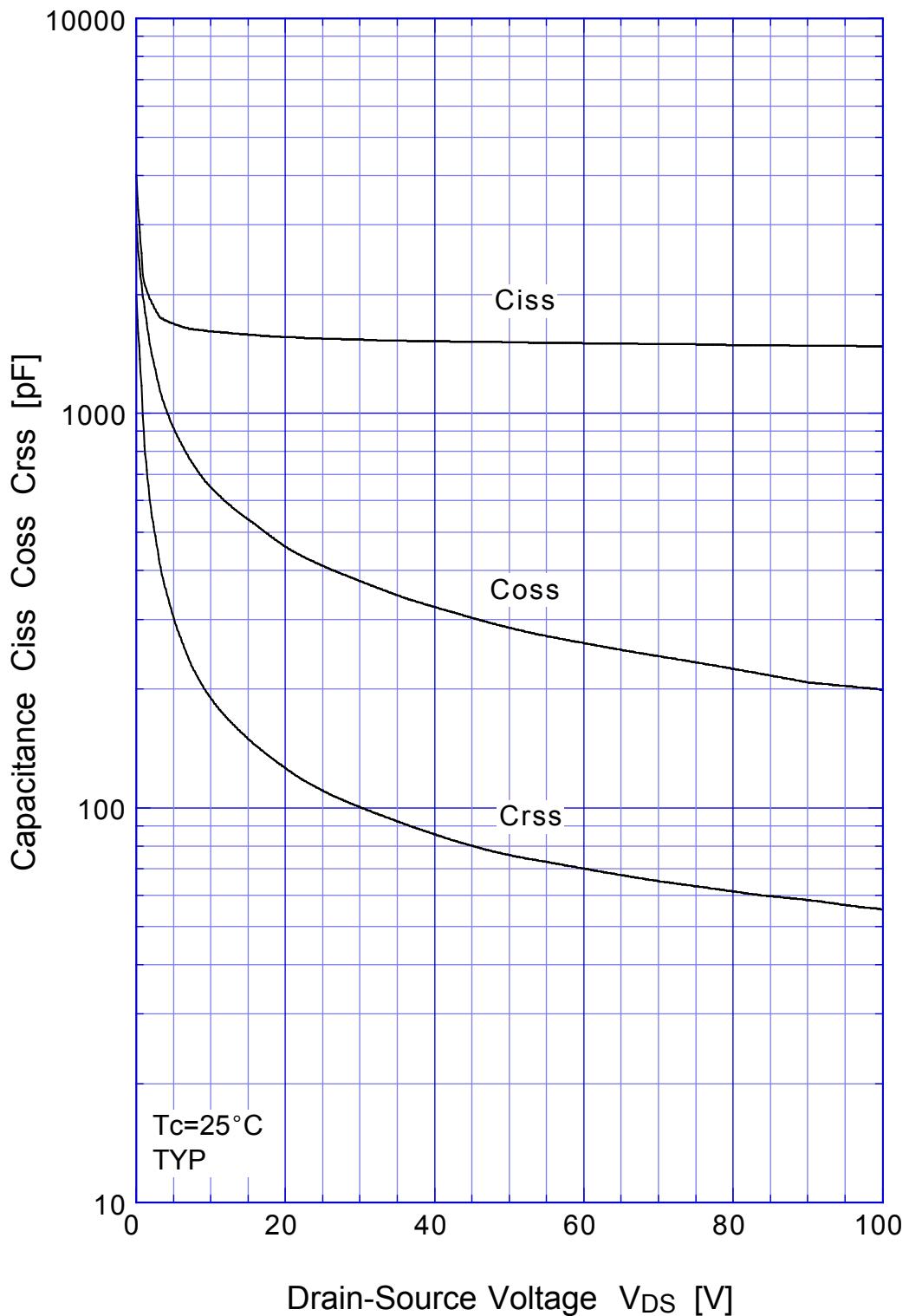
## 2SK2491 Safe Operating Area



## 2SK2491 Transient Thermal Impedance



**2SK2491** Capacitance



**2SK2491**

Power Derating



## 2SK2491

### Gate Charge Characteristics

